

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claim 1 (currently amended): A silicon-on-insulator semiconductor device comprising:
an insulative layer formed overlying a substrate;
a source region and a drain region formed overlying the insulative layer, the source region and the drain region comprising a material having a first conductivity type;
a body region disposed between the source region and the drain region and overlying the insulative layer, the body region comprising a material having a second conductivity type;
a gate insulative layer overlying the body region;
a gate region overlying the gate insulative layer;
a diode circuit comprising back to back diodes conductively coupled to the source region; and
a conductive connection coupling the gate region to the diode circuit.

Claim 2 (original): The device of Claim 1, wherein the conductive connection comprises:

a conductive region formed overlying the gate region; and
a metal trace coupling the conductive region to the diode circuit.

Claim 3 (original): The device of Claim 2, wherein the conductive region comprises a metallization layer.

Claim 4 (canceled)

Claim 5 (canceled)

Claim 6 (canceled)

Claim 7 (currently amended): The device of Claim 1 6, wherein the back-to-back diodes are separated from each other by an insulative region.

Claim 8 (currently amended): A silicon-on-insulator semiconductor device comprising:
an insulative layer formed overlying a substrate;
a source region and a drain region formed overlying the insulative layer, the
source region and the drain region comprising a material having a first conductivity type;
a body region disposed between the source region and the drain region and
overlying the insulative layer, the body region comprising a material having a second
conductivity type;
a gate insulative layer overlying the body region;
a gate region overlying the gate insulative layer;

a diode circuit conductively coupled to the source region; and
a conductive connection coupling the gate region to the diode circuit

~~The device of Claim 1~~, wherein the diode circuit comprises at least three diodes connected in series, each diode having a first region having the first conductivity type and a second region having the second conductivity type, the first region of a first one of the diodes conductively coupled to the source region and the second region of a second one of the diodes conductively coupled to the conductive connection.

Claim 9 (original): The device of Claim 1, wherein the source region and the drain region are formed from an n-type material.

Claim 10 (original): The device of Claim 1, wherein the source region and the drain region are formed from a p-type material.

Claim 11 (original): The device of Claim 1, wherein the insulative layer comprises oxide.

Claim 12 (withdrawn): A method for reducing charge damage in a silicon-on-insulator device comprising:

providing a silicon-on-insulator device having a source region and a drain region formed outwardly from an oxide layer, the oxide layer formed on a substrate and also having a gate region;

conductively coupling the source region to a diode circuit comprising at least one diode; and

conductively coupling the diode circuit to the gate region, thereby allowing charge to flow between the gate region and the source region during fabrication to prevent charge build-up, but preventing charge from flowing between the gate region and the service region during operation of the device.

Claim 13 (withdrawn): The method of Claim 12, wherein conductively coupling the source region to a diode circuit comprises conductively coupling the source region to a diode circuit having a pair of back-to-back diodes.

Claim 14 (withdrawn): The method of Claim 12, wherein conductively coupling the source region to a diode circuit comprises conductively coupling the source region to a diode circuit having at least three diodes connected in series.

Claim 15 (withdrawn): The method of Claim 12, wherein the silicon-on-insulator device further comprises a metallization layer conductively coupled to the gate region, and wherein conductively coupling the diode circuit to the gate region comprises conductively coupling the gate region to the diode circuit by a metal trace.

Claim 16 (withdrawn): The method of Claim 12, wherein the at least one diode comprises a single diode oriented with respect to the gate region and the source region

such that no current may flow from the gate region to the source region during operation of the transistor.

Claim 17 – 20 (canceled)